

# 2SK2756-01R

FUJI POWER MOSFET

## N-CHANNEL SILICON POWER MOSFET

### FAP-2S Series

#### Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

#### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

#### Maximum ratings and characteristic Absolute maximum ratings

(T<sub>c</sub>=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V <sub>DS</sub>	450	V
Continuous drain current	I <sub>D</sub>	±18	A
Pulsed drain current	I <sub>D(puls)</sub>	±72	A
Gate-source voltage	V <sub>GS</sub>	±35	V
Repetitive or non-repetitive	IAR *2	18	A
Maximum Avalanche Energy	EAS*1	100	mJ
Max. power dissipation	P <sub>D</sub>	85	W
Operating and storage temperature range	T <sub>ch</sub> T <sub>stg</sub>	+150 -55 to +150	°C

\*1 L=0.57mH, V<sub>cc</sub>=45V \*2 T<sub>ch</sub>≧150°C

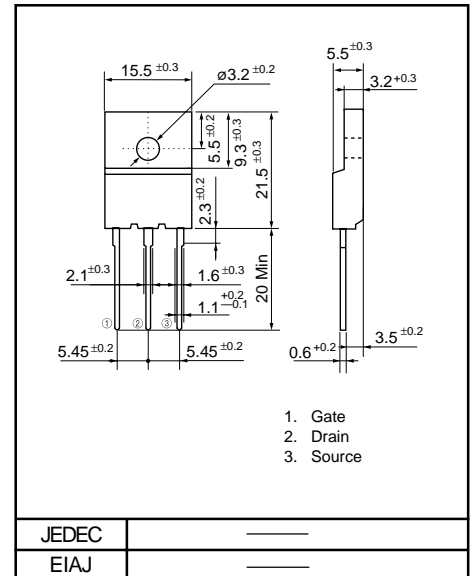
#### Electrical characteristics (T<sub>c</sub> =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA V <sub>GS</sub> =0V	450			V	
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =1mA V <sub>DS</sub> =V <sub>GS</sub>	3.5	4.0	4.5	V	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =450V V <sub>GS</sub> =0V	T <sub>ch</sub> =25°C		10	500	μA
			T <sub>ch</sub> =125°C		0.2	1.0	mA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±35V V <sub>DS</sub> =0V		10	100	nA	
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =9A V <sub>GS</sub> =10V		0.40	0.45	Ω	
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =9A V <sub>DS</sub> =25V	4.5	9.0		S	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1MHz		1400	2100	pF	
Output capacitance	C <sub>oss</sub>			250	380		
Reverse transfer capacitance	C <sub>rss</sub>			110	170		
Turn-on time t <sub>on</sub>	td(on)	V <sub>CC</sub> =300V I <sub>D</sub> =18A		30	50	ns	
	t <sub>r</sub>	V <sub>GS</sub> =10V		140	210		
Turn-off time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10Ω		80	120	ns	
	t <sub>f</sub>			60	90		
Avalanche capability	I <sub>AV</sub>	L=100μH T <sub>ch</sub> =25°C	18			A	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =2I <sub>DR</sub> V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.1	1.65	V	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>DR</sub>		500		ns	
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		6.5		μC	

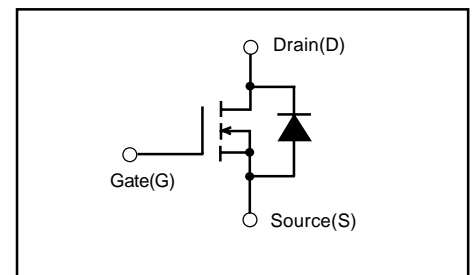
#### Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			1.56	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			30.0	°C/W

#### Outline Drawings



#### Equivalent circuit schematic



Characteristics

